

SILICON TRANSISTOR 2SC2351

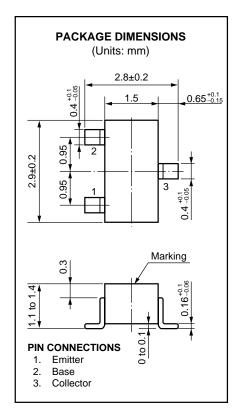
HIGH FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR MINI MOLD

FEATURES

NF 1.5 dB TYP. @ f = 1.0 GHz
 MAG 14 dB TYP. @ f = 1.0 GHz

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Collector to Base Voltage	Vсво	25	V
Collector to Emitter Voltage	VCEO	12	V
Emitter to Base Voltage	Vево	3.0	V
Collector Current	Ic	70	mΑ
Total Power Dissipation	Рт	250	mW
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	-65 to +150	°C



ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
CHARACTERISTIC	STIVIBUL	IVIIIN.	ITP.	WAA.	UNIT	TEST CONDITIONS
Collector Cutoff Current	Ісво			0.1	μΑ	Vcb = 15 V, IE = 0
Emitter Cutoff Current	ІЕВО			0.1	μΑ	V _{EB} = 2.0 V, I _C = 0
DC Current Gain	hfe	40		200		Vce = 10 V, Ic = 20 mA
Gain Bandwidth Product	f⊤		4.5		GHz	Vce = 10 V, Ic = 20 mA
Output Capacitance	Cob		0.75	1.0	pF	Vcb = 10 V, IE = 0, f = 1.0 MHz
Insertion Power Gain	S ₂₁ e ²	9	11		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz
Noise Figure	NF		1.5	3.0	dB	Vce = 10 V, Ic = 5 mA, f = 1.0 GHz
Maximum Available Gain	MAG		14		dB	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz

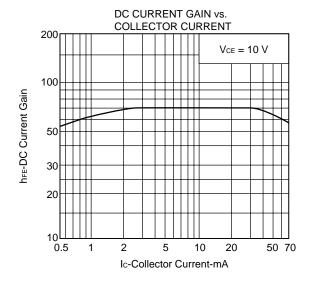
hfe Classification

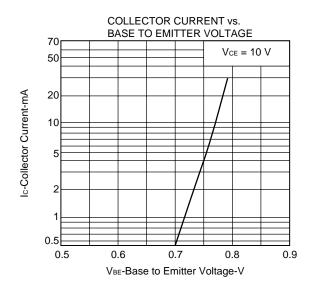
Class	E/P *	F/Q *		
Marking	R2	R3		
hfe	40 to 120	100 to 200		

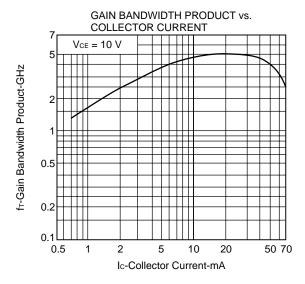
^{*} Old Specification / New Specification

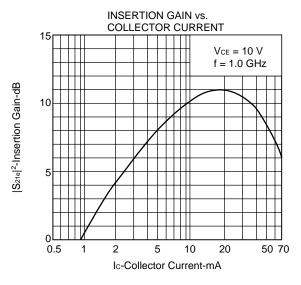


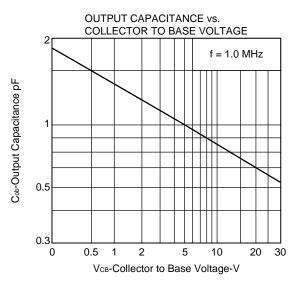
TYPICAL CHARACTERISTICS (TA = 25 °C)

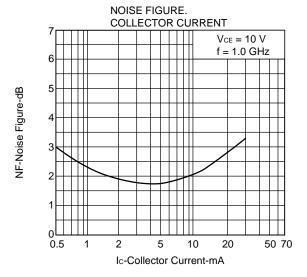


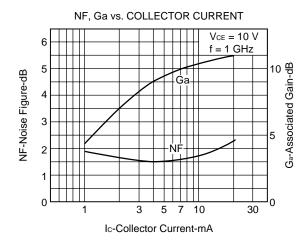












No part of this document may be copied or reproduced in any form or by any means without the prior written consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in this document.

NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property rights of third parties by or arising from use of a device described herein or any other liability arising from use of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other intellectual property rights of NEC Corporation or others.

While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.

NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.

M4 96.5

This datasheet has been downloaded from:

www. Data sheet Catalog.com

Datasheets for electronic components.